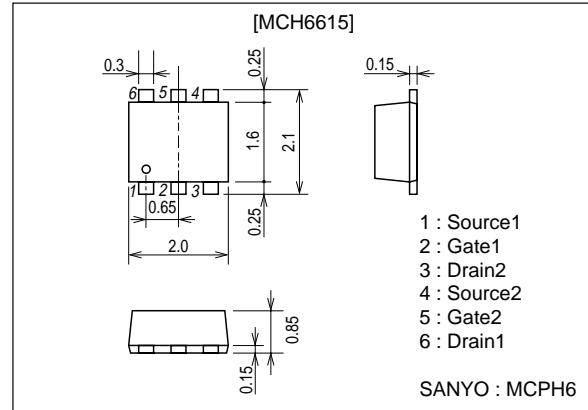


**MCH6615****Ultrahigh-Speed Switching Applications****Features**

- The MCH6615 incorporates two elements in the same package which are N-channel and P-channel low ON resistance and high-speed switching MOSFETs, thereby enabling high-density mounting.
- Low ON-resistance.
- 2.5V drive.

Package Dimensionsunit : mm
2173**Specifications****Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		30	-30	V
Gate-to-Source Voltage	V _{GSS}		±10	±10	V
Drain Current (DC)	I _D		0.65	-0.4	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	2.6	-1.6	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm)1unit	0.8		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0			10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =100μA	0.4		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =150mA	400	560		mS
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =150mA, V _{GS} =4V		0.9	1.2	Ω
	R _{DS(on)2}	I _D =80mA, V _{GS} =2.5V		1.2	1.7	Ω
	R _{DS(on)3}	I _D =10mA, V _{GS} =1.5V		2.6	5.2	Ω

Marking : FP

Continued on next page.

■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

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20101 TS IM TA-2910 No.6796-1/6

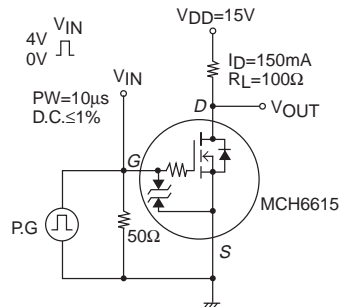
MCH6615

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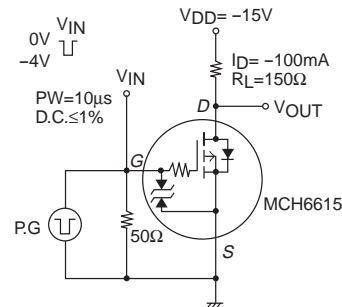
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		30		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		10		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit		32		ns
Rise Time	t _r	See specified Test Circuit		110		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit		250		ns
Fall Time	t _f	See specified Test Circuit		160		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =300mA		2.34		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =300mA		0.38		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =300mA		0.45		nC
Diode Forward Voltage	V _{SD}	I _S =300mA, V _{GS} =0		0.8	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0			-10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-100mA	210	300		mS
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-100mA, V _{GS} =-4V		2.4	3.1	Ω
	R _{DS(on)2}	I _D =-50mA, V _{GS} =-2.5V		3.5	4.9	Ω
	R _{DS(on)3}	I _D =-10mA, V _{GS} =-1.5V		10	20	Ω
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		28		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		5.2		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit		24		ns
Rise Time	t _r	See specified Test Circuit		75		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit		200		ns
Fall Time	t _f	See specified Test Circuit		150		ns
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-10V, I _D =-200mA		2		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-200mA		0.25		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-200mA		0.35		nC
Diode Forward Voltage	V _{SD}	I _S =-200mA, V _{GS} =0		-0.82	-1.2	V

Switching Time Test Circuit

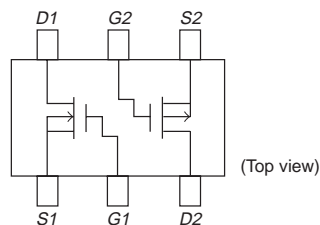
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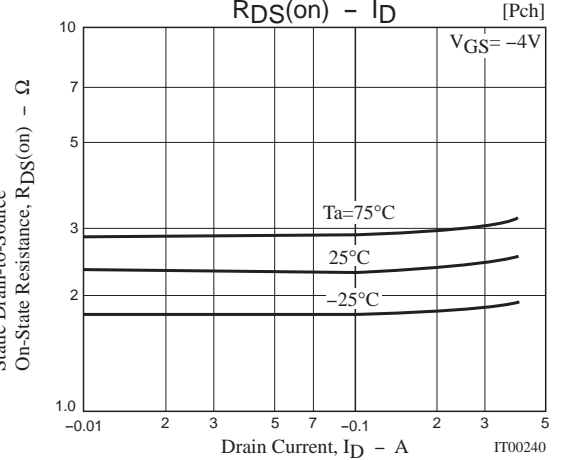
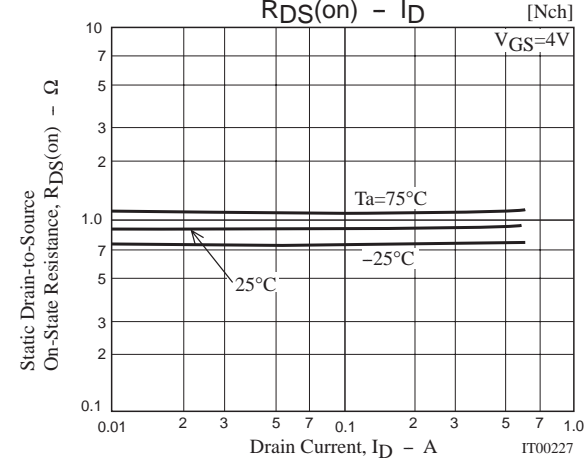
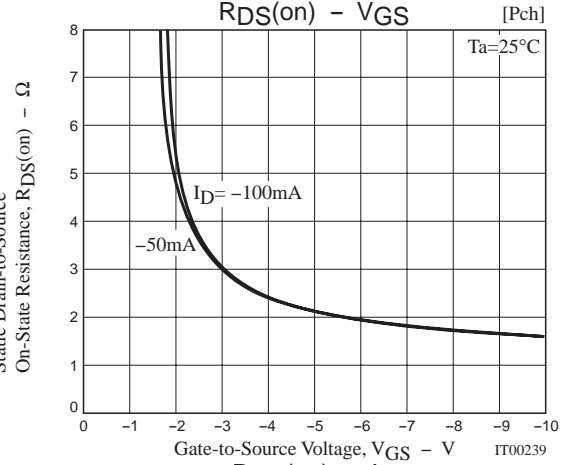
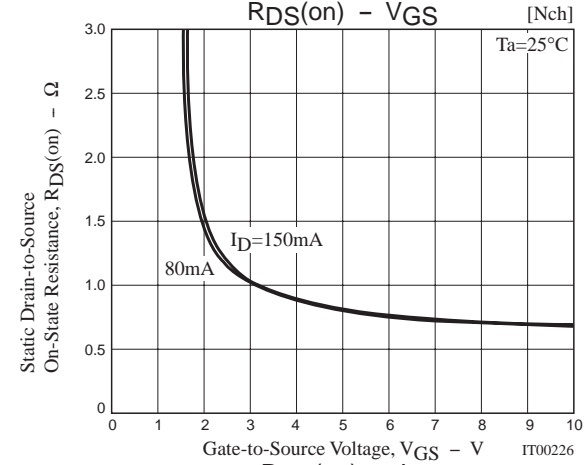
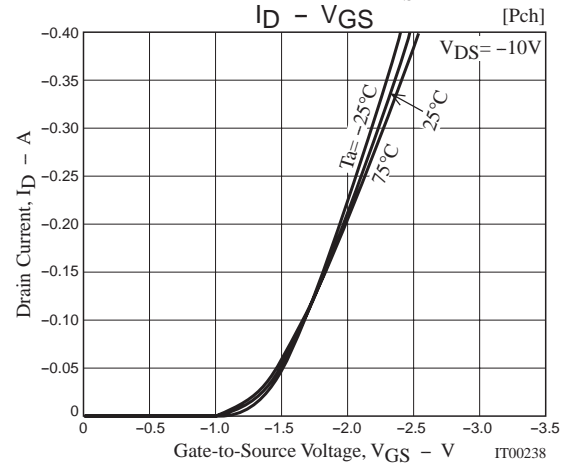
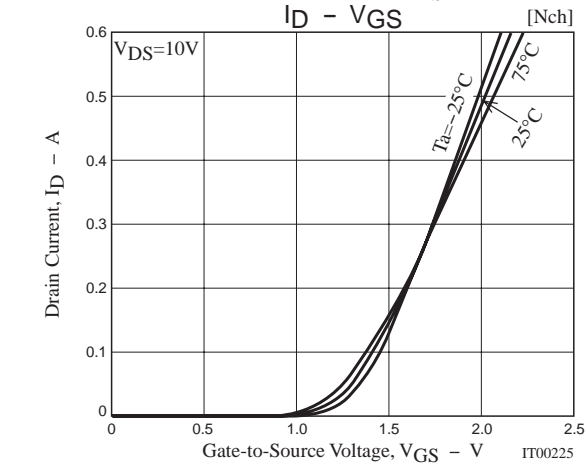
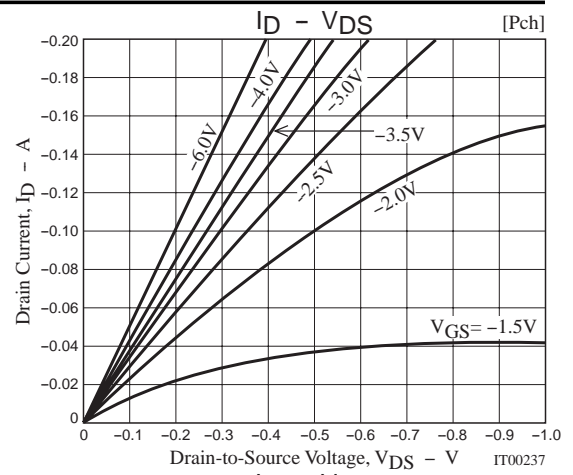
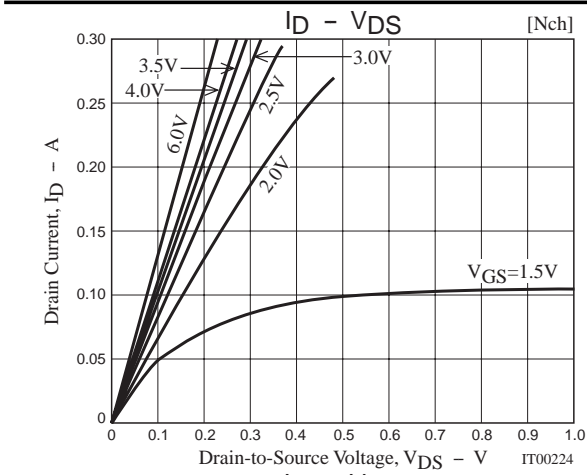
[P-channel]



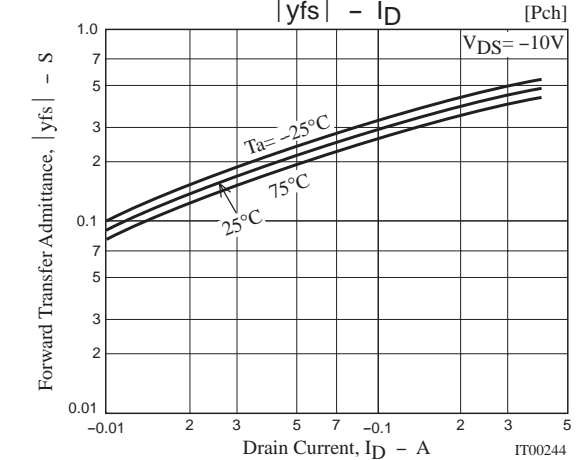
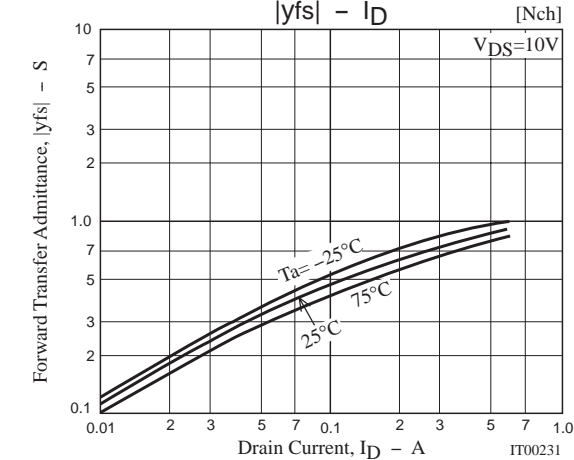
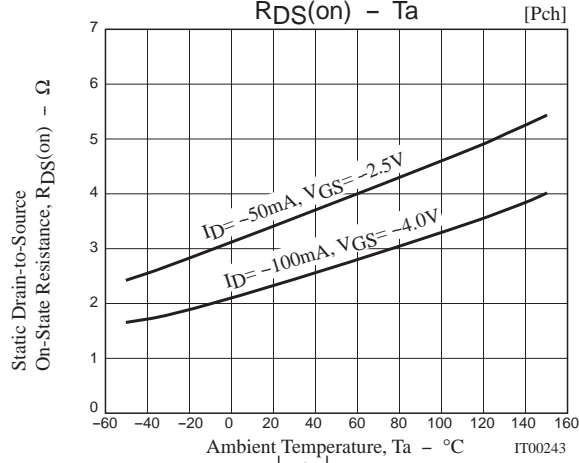
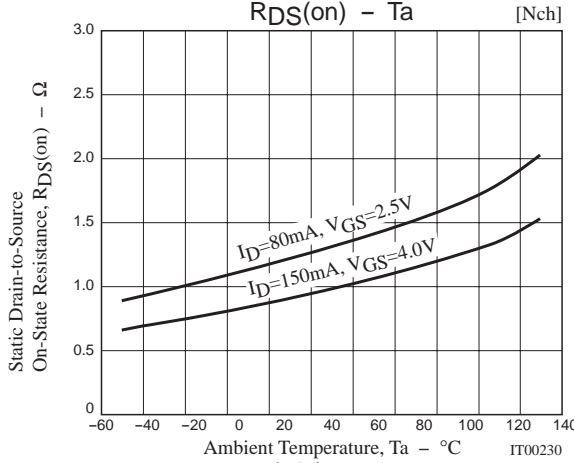
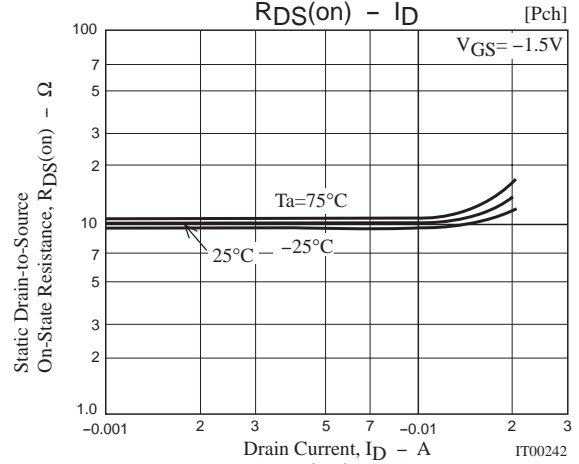
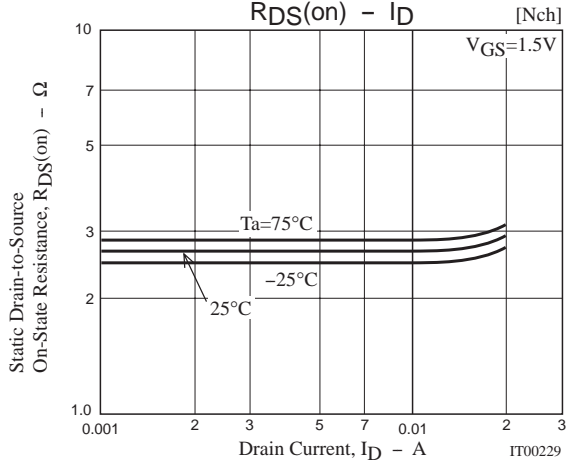
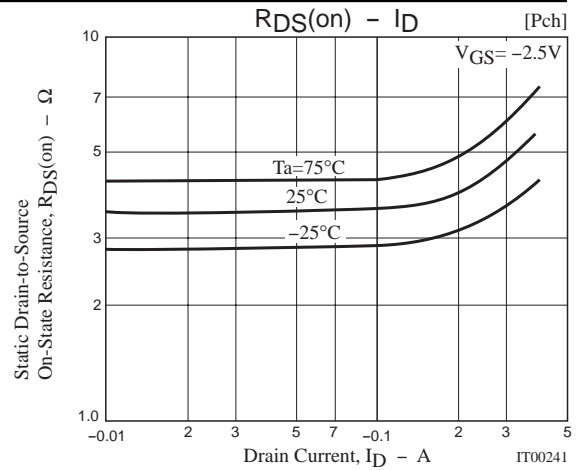
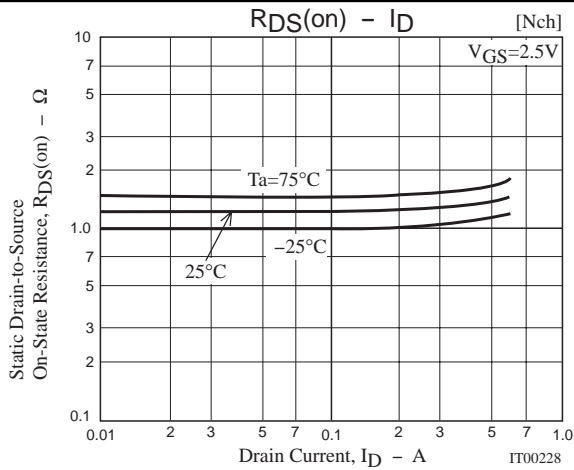
Electrical Connection



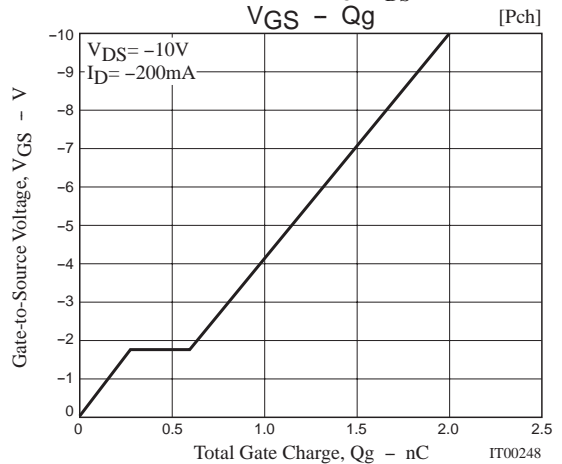
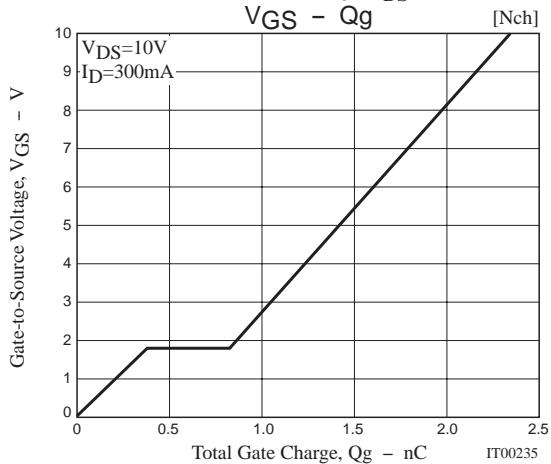
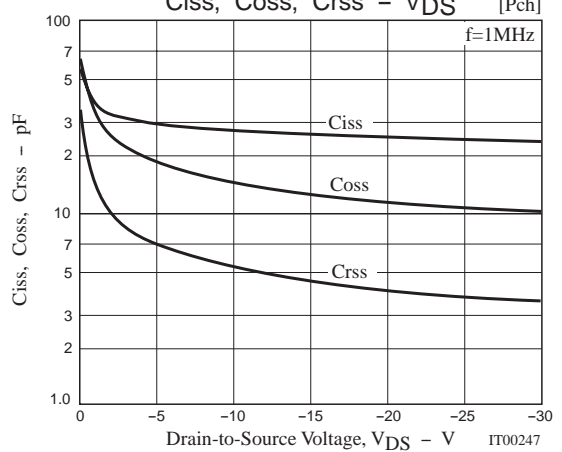
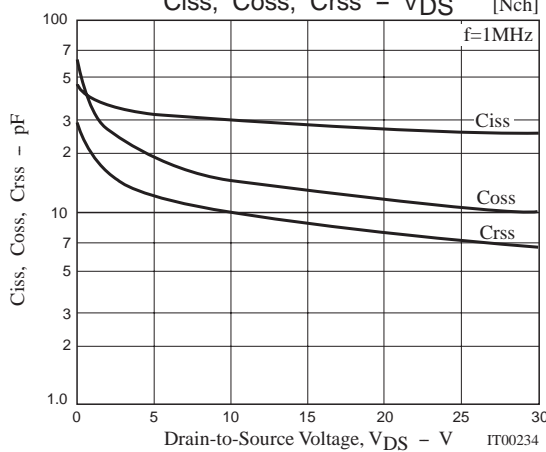
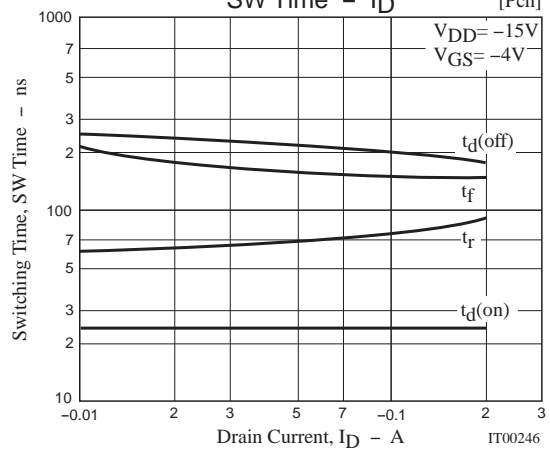
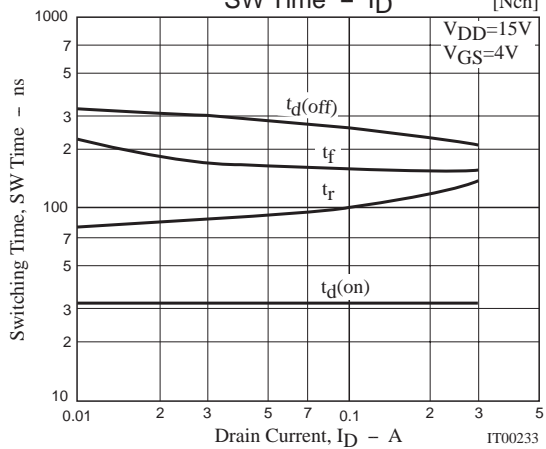
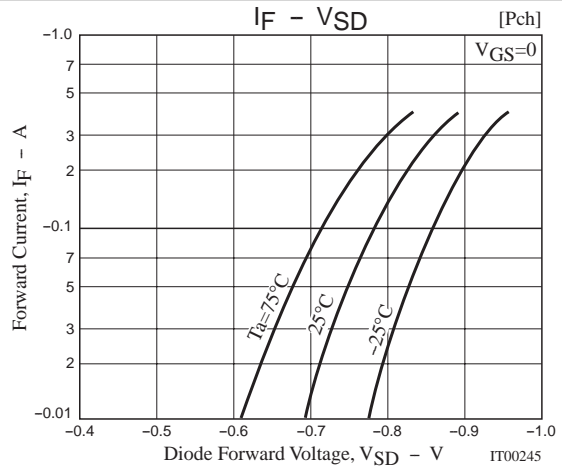
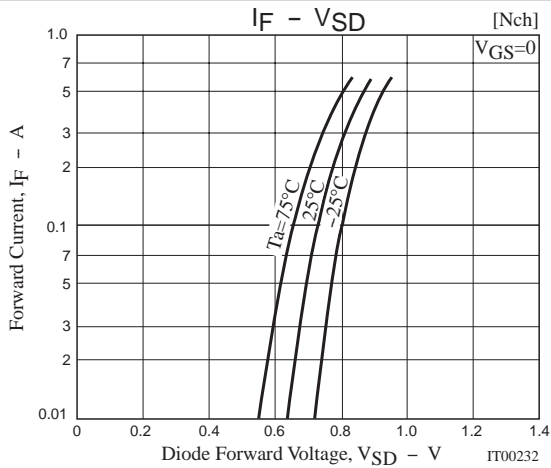
MCH6615



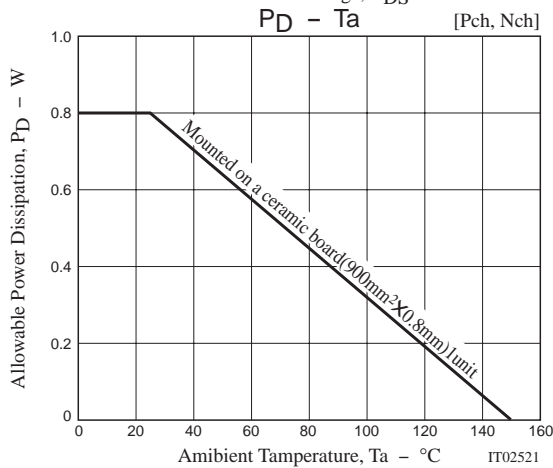
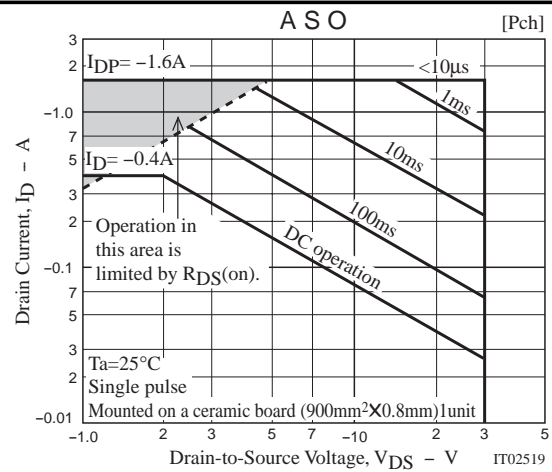
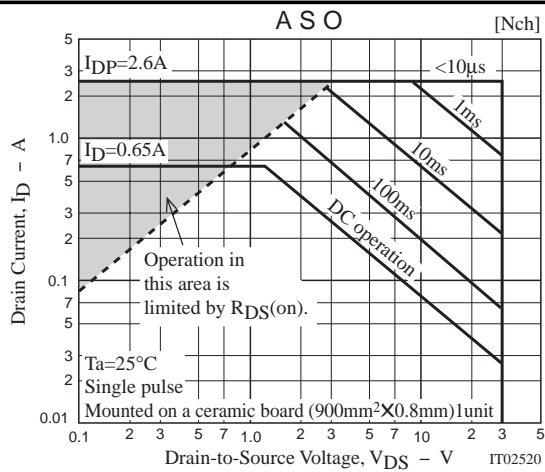
MCH6615



MCH6615



MCH6615



Note on usage : Since the MCH6615 is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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